

IN THE CLAIMS:

None of the claims have been amended herein. All of the pending claims 1 through 19 are presented below for convenience of the Examiner. This listing of claims will replace all prior versions and listings of claims in the application. Please enter these claims as previously amended.

1. (Previously presented) A selective method for cleaning material from a wafer comprising:
providing an etchant-dispensing apparatus having an inlet thereto for an etchant agent and a tubular member having at least one thin annular edge thereon to clean material from the wafer;
placing an area of the wafer within an annular member of the etchant-dispensing apparatus, at least one thin annular edge of the annular member of the etchant-dispensing apparatus located adjacent a portion of the wafer to clean material from the wafer;
aligning the wafer and the etchant-dispensing apparatus to clean material from the wafer;
dispensing an etchant through another tubular member having a portion thereof surrounded by the tubular member having at least one thin annular edge thereon onto the area of the wafer using the etchant-dispensing apparatus to clean material from the wafer; and
removing the etchant.
2. (Previously presented) The method of claim 1, wherein placing includes aligning the wafer in a substantially perpendicular position in relation to the etchant-dispensing apparatus.
3. (Previously presented) The method of claim 1, wherein aligning comprises aligning the wafer to the etchant-dispensing apparatus.
4. (Previously presented) The method of claim 1, wherein aligning comprises aligning the etchant-dispensing apparatus to the wafer.

5. (Previously presented) The method of claim 1, wherein aligning comprises aligning the wafer substantially perpendicular to the at least one thin annular edge of the annular member of the etchant-dispensing apparatus.

6. (Previously presented) The method of claim 1, wherein aligning includes aligning the at least one thin annular edge of the annular member of the etchant-dispensing apparatus substantially perpendicular to a portion of the wafer adjacent the area thereon.

7. (Previously presented) The method of claim 1, wherein the material includes at least one of chemical mechanical planarization process slurry material, a metal material, a photoresist material, a dielectric material, and a polysilicon material.

8. (Previously presented) The method of claim 7, wherein the metal material includes a refractory metal.

9. (Previously presented) The method of claim 1, wherein removing the etchant includes removal of the etchant by one of suction and vacuum.

10. (Previously presented) The method of claim 1, further comprising cleaning a surface of the wafer.

11. (Previously presented) The method of claim 10, wherein cleaning the surface of the wafer includes:
cleaning the surface of the wafer with a cleaning agent; and
rinsing the wafer in deionized water.

12. (Previously presented) The method of claim 1, wherein the etchant includes at least one of a liquid, a liquid vapor, a gas, ammonia, hydrogen fluoride, nitric acid, hydrogen peroxide, ammonium fluoride, and mixtures thereof.

13. (Previously presented) A selective cleaning method for removing a material from a wafer for a semiconductor fabrication process, the method comprising:
chemical mechanical planarizing the wafer prior to removing the material from the wafer;
providing an etchant-dispensing apparatus having a tubular member, an annular member having at least one thin annular edge thereon, and an inlet for etchant for selectively removing a material from a wafer;
aligning at least one area of the wafer and at least a portion of the etchant-dispensing apparatus for selectively removing a material from a wafer;
dispensing an etchant through another tubular member having a portion thereof surrounded by the tubular member having at least one thin annular edge thereon onto the at least one area of the wafer for selectively removing a material from a wafer; and
removing the etchant using a portion of the etchant-dispensing apparatus for selectively removing a material from a wafer.

14. (Previously presented) The method of claim 13, wherein aligning includes one of aligning a portion of the wafer in a substantially perpendicular position in relation to the etchant-dispensing apparatus, aligning a portion of the wafer to the etchant-dispensing apparatus, aligning the etchant-dispensing apparatus to the wafer, and aligning the wafer substantially perpendicular to the at least one thin annular edge of annular member of the etchant-dispensing apparatus.

15. (Previously presented) The method of claim 13, wherein the material includes at least one of chemical mechanical planarization process slurry material, a metal material, a photoresist material, a dielectric material, and a polysilicon material.

16. (Previously presented) The method of claim 15, wherein the metal material includes a refractory metal.

17. (Previously presented) The method of claim 13, wherein removing the etchant includes removal of the etchant by one of suction and vacuum.

18. (Previously presented) The method of claim 13, further comprising cleaning a surface of the wafer.

19. (Previously presented) The method of claim 18, wherein cleaning a surface of the wafer includes:
cleaning the surface of the wafer with a cleaning agent; and
rinsing the wafer in deionized water.